

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Ξ·ΧΕΙ

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104lcafp-x0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

(1/5)

Pin count	Package	Fields of Application Note	Ordering Part Number
30 pins	30-pin plastic LSSOP	A	R5F104AAASP#V0, R5F104ACASP#V0, R5F104ADASP#V0, R5F104AEASP#V0,
	(7.62 mm (300), 0.65 mm pitch)		R5F104AFASP#V0, R5F104AGASP#V0
			R5F104AAASP#X0, R5F104ACASP#X0, R5F104ADASP#X0, R5F104AEASP#X0, R5F104AEASP#X0, R5F104ACASP#X0
		D	
		D	R5F104AFDSP#V0, R5F104AGDSP#V0
			R5F104AADSP#X0, R5F104ACDSP#X0, R5F104ADDSP#X0, R5F104AEDSP#X0,
			R5F104AFDSP#X0, R5F104AGDSP#X0
		G	R5F104AAGSP#V0, R5F104ACGSP#V0, R5F104ADGSP#V0, R5F104AEGSP#V0, R5F104AFGSP#V0, R5F104AGGSP#V0
			R5F104AAGSP#X0, R5F104ACGSP#X0, R5F104ADGSP#X0, R5F104AEGSP#X0, R5F104AFGSP#X0, R5F104AGGSP#X0
32 pins	32-pin plastic HWQFN (5 \times 5 mm, 0.5 mm pitch)	A	R5F104BAANA#U0, R5F104BCANA#U0, R5F104BDANA#U0, R5F104BEANA#U0, R5F104BFANA#U0, R5F104BGANA#U0
			R5F104BAANA#W0, R5F104BCANA#W0, R5F104BDANA#W0, R5F104BEANA#W0, R5F104BFANA#W0, R5F104BGANA#W0
		D	R5F104BADNA#U0, R5F104BCDNA#U0, R5F104BDDNA#U0, R5F104BEDNA#U0,
			R5F104BFDNA#U0, R5F104BGDNA#U0
			R5F104BADNA#W0, R5F104BCDNA#W0, R5F104BDDNA#W0, R5F104BEDNA#W0,
		G	RSF104BFDINA#W0, RSF104BGDINA#W0
		0	R5F104BFGNA#U0, R5F104BGGNA#U0
			R5F104BAGNA#W0, R5F104BCGNA#W0, R5F104BDGNA#W0, R5F104BEGNA#W0, R5F104BFGNA#W0, R5F104BGGNA#W0
	32-pin plastic LQFP $(7 \times 7, 0.8 \text{ mm pitch})$	A	R5F104BAAFP#V0, R5F104BCAFP#V0, R5F104BDAFP#V0, R5F104BEAFP#V0, R5F104BFAFP#V0, R5F104BGAFP#V0
			R5F104BAAFP#X0, R5F104BCAFP#X0, R5F104BDAFP#X0, R5F104BEAFP#X0, R5F104BEAFP#X0, R5F104BGAFP#X0
		D	R5F104BADFP#V0, R5F104BCDFP#V0, R5F104BDDFP#V0, R5F104BEDFP#V0, R5F104BEDFP#V0, R5F104BGDFP#V0
			R5F104BADFP#X0, R5F104BCDFP#X0, R5F104BDDFP#X0, R5F104BEDFP#X0, R5F104BEDFP#X0, R5F104BGDFP#X0
		G	R5F104BAGFP#V0, R5F104BCGFP#V0, R5F104BDGFP#V0, R5F104BEGFP#V0, R5F104BFGFP#V0, R5F104BGGFP#V0
			R5F104BAGFP#X0, R5F104BCGFP#X0, R5F104BDGFP#X0, R5F104BEGFP#X0, R5F104BFGFP#X0, R5F104BGGFP#X0
36 pins	36-pin plastic WFLGA (4 \times 4 mm, 0.5 mm pitch)	A	R5F104CAALA#U0, R5F104CCALA#U0, R5F104CDALA#U0, R5F104CEALA#U0, R5F104CFALA#U0, R5F104CGALA#U0
			R5F104CAALA#W0, R5F104CCALA#W0, R5F104CDALA#W0, R5F104CEALA#W0, R5F104CFALA#W0, R5F104CGALA#W0
		G	R5F104CAGLA#U0, R5F104CCGLA#U0, R5F104CDGLA#U0, R5F104CEGLA#U0, R5F104CFGLA#U0, R5F104CGGLA#U0
			R5F104CAGLA#W0, R5F104CCGLA#W0, R5F104CDGLA#W0, R5F104CEGLA#W0, R5F104CFGLA#W0, R5F104CGGLA#W0

Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



• 64-pin plastic FLGA (5 × 5 mm, 0.5 mm pitch)



	A	В	С	D	E	F	G	Н	
0	EV _{DD0}	EVss0	P121/X1	P122/X2/	P137/INTP0	P123/XT1	P124/XT2/	P120/ANI19/	
8				EXCLK			EXCLKS	VCOUT0 Note 1	8
	P60/SCLA0	Vdd	Vss	REGC	RESET	P01/TO00/	P00/TI00/	P140/	
7					-	TRGCLKB/	TRGCLKA/	PCLBUZ0/	7
						TRJIO0	(TRJO0)	INTP6	
	P61/SDAA0	P62/SSI00	P63	P40/TOOL0	P41/(TRJIO0)	P43/(INTP9)	P02/ANI17/	P141/	
6							SO10/TxD1	PCLBUZ1/	6
								INTP7	
	P77/KR7/	P31/TI03/	P53/(INTP2)	P42/(INTP8)	P03/ANI16/	P04/SCK10/	P130	P20/ANI0/	
5	INTP11/(TXD2)	TO03/INTP4/			SI10/RxD1/	SCL10		AVREFP	5
5		(PCLBUZ0)/			SDA10				J
		(TRJIO0)							
	P75/KR5/	P76/KR6/	P52/(INTP1)	P54/(INTP3)	P16/TI01/	P21/ANI1/	P22/ANI2/	P23/ANI3/	
	INTP9/	INTP10/			TO01/INTP5/	AVREFM	ANO0 Note 1	ANO1 Note 1	
4	SCK01/	(RXD2)			TRDIOC0/				4
	SCL01				IVREF0 Note 1/				
					(SI00)/(RXD0)				
	P70/KR0/	P73/KR3/	P74/KR4/	P17/TI02/TO02/	P15/SCK20/	P12/SO11/	P24/ANI4	P26/ANI6	
	SCK21/	SO01	INTP8/SI01/	TRDIOA0/	SCL20/	TRDIOB1/			
3	SCL21		SDA01	TRDCLK/	TRDIOB0/	IVREF1 Note 1/			3
				IVCMP0 Note 1/	(SDAA0)	(INTP5)/			
				(SO00)/(TXD0)		(TxD0_1) Note 2			
	P30/INTP3/	P72/KR2/	P71/KR1/	P06/(INTP11)/	P14/RxD2/	P11/SI11/	P25/ANI5	P27/ANI7	
2	RTC1HZ/	SO21	SI21/SDA21	(TRJIO0)	SI20/SDA20/	SDA11/			2
2	SCK00/				TRDIOD0/	TRDIOC1/			2
	SCL00/TRJO0				(SCLA0)	(RxD0_1) Note 2			
	P05/(INTP10)	P50/INTP1/	P51/INTP2/	P55/	P13/TxD2/	P10/SCK11/	P146	P147/ANI18/	
		SI00/RxD0/	SO00/TxD0/	(PCLBUZ1)/	SO20/	SCL11/		VCOUT1 Note 1	
1		TOOLRxD/	TOOLTxD/	(SCK00)/	TRDIOA1/	TRDIOD1			1
•		SDA00/	TRGIOB	(INTP4)	IVCMP1 Note 1				Ċ
		TRGIOA/							
		(TRJO0)							
	Α	В	С	D	E	F	G	Н	

Note 1. Mounted on the 96 KB or more code flash memory products.

Note 2. Mounted on the 384 KB or more code flash memory products.

Caution 1. Make EVsso pin the same potential as VSS pin.

Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.

Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.

Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

RENESAS

1.5.4 40-pin products



Note Mounted on the 96 KB or more code flash memory products.



Note	The flash library uses RAM in self-programming and rewriting of the data flash memory.
	The target products and start address of the RAM areas used by the flash library are shown below.
	R5F104xD (x = A to C, E to G, J, L): Start address FE900H
	R5F104xE (x = A to C, E to G, J, L): Start address FE900H
	For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family
	(R20UT2944).



2.3 DC Characteristics

2.3.1 Pin characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	$1.6 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}$			-10.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	$4.0~V \leq EV \text{DD0} \leq 5.5~V$			-55.0	mA
		P102, P120, P130, P140 to P145 (When duty < 70% Note 3)	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			-10.0	mA
		(when $auty \leq 70\%$ Note 5)	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			-5.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% ^{Note 3})	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-80.0	mA
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 4.0 \text{ V}$			-19.0	mA
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			-10.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			-5.0	mA
		Total of all pins (When duty \leq 70% ^{Note 3})	$1.6 \text{ V} \le \text{EVDD0} \le 5.5 \text{ V}$			-135.0 Note 4	mA
	Іон2	Per pin for P20 to P27, P150 to P156	$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			-0.1 Note 2	mA
		Total of all pins (When duty \leq 70% ^{Note 3})	$1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDD0, EVDD1, VDD pins to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$ <Example> Where n = 80% and IOH = -10.0 mA Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Note 4. -100 mA for industrial applications (R5F104xxDxx, R5F104xxGxx).

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.



Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	loL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			70.0	mA
		P102, P120, P130, P140 to P145	$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
		(When duty \leq 70% ^{Note 3})	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			9.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			4.5	mA
		Total of P05, P06, P10 to P17,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			80.0	mA
		P30, P31, P50 to P57,	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P60 to P67, P70 to P77, P80 to P87, P100, P101, P110	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			20.0	mA
		P111, P146, P147 (When duty \leq 70% ^{Note 3})	1.6 V ≤ EVDD0 < 1.8 V			10.0	mA
		Total of all pins (When duty \leq 70% ^{Note 3})				150.0	mA
	IOL2	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty \leq 70% ^{Note 3})	$1.6 V \le VDD \le 5.5 V$			5.0	mA

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/5)

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1, and Vss pins.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoL \times 0.7)/(n \times 0.01)
- <Example> Where n = 80% and IoL = 10.0 mA
 - Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage cur- rent, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVDDO				1	μA
	Ilih2	P20 to P27, P137, P150 to P156, RESET	VI = VDD				1	μA
	Ilih3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator con- nection			10	μA
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	VI = VSS				-1	μA
	Ililis	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μA
				In resonator con- nection			-10	μA
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVsso	, In input port	10	20	100	kΩ

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(5/5)

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	ymbol Conditions							MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fносо = 64 MHz,	Basic	VDD = 5.0 V		2.9		mA
current		ing mode	mode Note 5	fiн = 32 MHz Note 3	operation	VDD = 3.0 V		2.9		
NOLE 1				fносо = 32 MHz,	Basic	VDD = 5.0 V		2.5		
				fiн = 32 MHz Note 3	operation	VDD = 3.0 V		2.5		
			HS (high-speed main)	fносо = 64 MHz,	Normal	VDD = 5.0 V		6.0	11.2	mA
			mode Note 5	fiH = 32 MHz Note 3	operation	VDD = 3.0 V		6.0	11.2	
				fносо = 32 MHz,	Normal	VDD = 5.0 V		5.5	10.6	
				fiн = 32 MHz Note 3	operation	VDD = 3.0 V		5.5	10.6	
				fносо = 48 MHz,	Normal	VDD = 5.0 V		4.7	8.6	
				fiн = 24 MHz Note 3	operation	VDD = 3.0 V		4.7	8.6	
				fносо = 24 MHz,	Normal	VDD = 5.0 V		4.4	8.2	
				fin = 24 MHz Note 3	operation	VDD = 3.0 V		4.4	8.2	
				fносо = 16 MHz,	Normal	VDD = 5.0 V		3.3	5.9	
				fiн = 16 MHz ^{Note 3}	operation	VDD = 3.0 V		3.3	5.9	
			LS (low-speed main)	fносо = 8 MHz,	Normal	VDD = 3.0 V		1.5	2.5	mA
			mode Note 5	fin = 8 MHz Note 3	operation	VDD = 2.0 V		1.5	2.5	
			LV (low-voltage main)	fносо = 4 MHz,	Normal	VDD = 3.0 V		1.5	2.1	mA
			mode Note 5	fin = 4 MHz Note 3	operation	VDD = 2.0 V		1.5	2.1	
			HS (high-speed main)	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.7	6.8	mA
			mode Note 5	VDD = 5.0 V	operation	Resonator connection		3.9	7.0	
			f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.7	6.8		
				VDD = 3.0 V	operation	Resonator connection		3.9	7.0	-
				f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
				f _{MX} = 10 MHz ^{Note 2} ,	Normal	Square wave input		2.3	4.1	
				VDD = 3.0 V	operation	Resonator connection		2.3	4.2	
			LS (low-speed main)	f _{MX} = 8 MHz ^{Note 2} ,	Normal	Square wave input		1.4	2.4	mA
			mode Note 5	VDD = 3.0 V	operation	Resonator connection		1.4	2.5	
				f _{MX} = 8 MHz ^{Note 2} ,	Normal	Square wave input		1.4	2.4	
				V _{DD} = 2.0 V	operation	Resonator connection		1.4	2.5	
			Subsystem clock	fsue = 32.768 kHz Note 4	Normal	Square wave input		5.2		μΑ
			operation	TA = -40°C	operation	Resonator connection		5.2		
				fsue = 32.768 kHz Note 4	Normal	Square wave input		5.3	7.7	
				TA = +25°C	operation	Resonator connection		5.3	7.7	
				fsue = 32.768 kHz Note 4	Normal	Square wave input		5.5	10.6	
			T ₄ fs	TA = +50°C	operation	Resonator connection		5.5	10.6]
				fsub = 32.768 kHz Note 4	Normal	Square wave input		5.9	13.2	
		Tr	TA = +70°C	operation	Resonator connection		6.0	13.2		
				fsub = 32.768 kHz Note 4	Normal	Square wave input		6.8	17.5	
					TA = +85°C	operation	Resonator connection		6.9	17.5

(Notes and Remarks are listed on the next page.)



CSI mode connection diagram (during communication at different potential



- **Remark 1.** Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
- Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



Parameter	Symbol	Conditions	HS (high- n	speed main) node	LS (low-s	speed main) 10de	LV (low-v m	oltage main) node	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	t
SCLr clock frequency	fscL	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{array}$		400 Note 1		300 Note 1		300 Note 1	kHz
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		400 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:VD} \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2}, \\ C_b = 100 \ \text{pF}, \ R_b = 5.5 \ \text{k}\Omega \end{array}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t∟ow		475		1550		1550		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	475		1550		1550		ns
			1150		1550		1550		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1150		1550		1550		ns
		$\label{eq:linear} \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2}, \\ & C_b = 100 \ \text{pF}, \ R_b = 5.5 \ \text{k}\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	245		610		610		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	200		610		610		ns
			675		610		610		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	600		610		610		ns
			610		610		610		ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified l²C mode) (TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$1.8 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$		1.2	±7.0	LSB
			$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}^{\text{Note 3}}$		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \le V_{DD} \le 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$1.8~V \le V_{DD} \le 5.5~V$	17		39	μs
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μs
		10-bit resolution	$3.6~V \le V_{DD} \le 5.5~V$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		(HS (high-speed main) mode)	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$1.8~V \le V_{DD} \le 5.5~V$			±0.60	%FSR
			1.6 V \leq VDD \leq 5.5 V Note 3			±0.85	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8~V \le V_{DD} \le 5.5~V$			±4.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±6.5	LSB
Differential linearity error	DLE	10-bit resolution	$1.8~V \le V_{DD} \le 5.5~V$			±2.0	LSB
Note 1			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		Vdd	V
		ANI16 to ANI20				EV _{DD0}	V
		Internal reference voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) mode)			V _{BGR} Note 4		
		Temperature sensor output voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) mode)			V _{TMPS25} Note 4		

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



Absolute Maximum Ratings

(2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
		170 mA	P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	Та	In normal o	peration mode	-40 to +105	°C
temperature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- **Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 32 MHz
 - 2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsuB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. During HALT instruction execution by flash memory.
- **Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7.Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: $2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$ @1 MHz to 32 MHz
 - 2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fill: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



Parameter Symbo Conditions MIN. TYP. MAX. fносо = 64 MHz, $V_{DD} = 5.0 V$ 2.6 Supply DD1 Operat-HS (high-speed main) Basic current ing mode mode Note 5 fill = 32 MHz Note 3 operation VDD = 3.0 V 2.6 Note 1 fносо = 32 MHz. Basic VDD = 5.0 V 2.3 fiH = 32 MHz Note 3 operation VDD = 3.0 V 2.3 fносо = 64 MHz, VDD = 5.0 V HS (high-speed main) Normal 5.4 10.9 mode Note 5 fiH = 32 MHz Note 3 operation $V_{DD} = 3.0 V$ 54 10.9 VDD = 5.0 V 10.3 fносо = 32 MHz. Normal 5.0 fin = 32 MHz Note 3 operation VDD = 3.0 V 10.3 5.0 VDD = 5.0 V fHOCO = 48 MHz. 42 82 Normal fiH = 24 MHz Note 3 operation VDD = 3.0 V 4.2 8.2 fносо = 24 MHz, Normal VDD = 5.0 V 4.0 7.8 fill = 24 MHz Note 3 operation VDD = 3.0 V 40 78 fносо = 16 MHz, Normal VDD = 5.0 V 3.0 5.6 fin = 16 MHz Note 3 operation VDD = 3.0 V 3.0 5.6 HS (high-speed main) 3.4 f_{MX} = 20 MHz Note 2 Normal Square wave input 6.6 mode Note 5 VDD = 5.0 V operation Resonator connection 3.6 6.7 f_{MX} = 20 MHz Note 2, Normal Square wave input 34 6.6 operation $V_{DD} = 3.0 V$ Resonator connection 3.6 6.7 fmx = 10 MHz Note 2, 2.1 3.9 Normal Square wave input VDD = 5.0 V operation Resonator connection 22 4.0 f_{MX} = 10 MHz Note 2. Normal Square wave input 2.1 3.9 VDD = 3.0 V operation Resonator connection 2.2 4.0 fsub = 32.768 kHz Note 4 49 71 Subsystem clock Normal Square wave input operation operation $T_A = -40^{\circ}C$ Resonator connection 4.9 7.1 fsub = 32.768 kHz Note 4 Normal Square wave input 4.9 7.1 $T_A = +25^{\circ}C$ operation 4.9 7.1 Resonator connection Normal 5.1 8.8 fsub = 32.768 kHz Note 4 Square wave input $T_A = +50^{\circ}C$ operation 8.8 Resonator connection 5.1 10.5 fsub = 32.768 kHz Note 4 Square wave input 5.5 Normal TA = +70°C operation Resonator connection 5.5 10.5 fsub = 32.768 kHz Note 4 Normal 6.5 14.5 Square wave input TA = +85°C operation 6.5 14.5 Resonator connection

fsub = 32.768 kHz Note 4

 $T_{A} = +105^{\circ}C$

Normal

operation

Square wave input

Resonator connection

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(Notes and Remarks are listed on the next page.)

Unit

mΑ

mΑ

mΑ

μΑ

13.0

13.0

58.0

58.0

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, fal	ling reset voltage	2.64	2.75	2.86	V
threshold	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	VIS1, LVIS0 = 0, 1 Rising release reset voltage		3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	Vlvdd3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

(2) Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, VSS = 0 V)

3.6.7 Power supply voltage rising slope characteristics

(TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.



R5F104BAAFP, R5F104BCAFP, R5F104BDAFP, R5F104BEAFP, R5F104BFAFP, R5F104BGAFP R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BFDFP, R5F104BGDFP R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP





NOTE

Dimensions "%1" and "%2" do not include mold flash.
Dimension "%3" does not include trim offset.

© 2012 Renesas Electronics Corporation. All rights reserved.

е

у

0.80

0.20

0.10



R5F104GKAFB, R5F104GLAFB R5F104GKGFB, R5F104GLGFB





4.10 100-pin products

R5F104PFAFB, R5F104PGAFB, R5F104PHAFB, R5F104PJAFB R5F104PFDFB, R5F104PGDFB, R5F104PHDFB, R5F104PJDFB R5F104PFGFB, R5F104PGGFB, R5F104PHGFB, R5F104PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]	
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69	



©2012 Renesas Electronics Corporation. All rights reserved.



REVISION HISTORY

RL78/G14 Datasheet

Rev. Date	Data	Description			
	Dale	Page	Summary		
0.01	Feb 10, 2011	—	First Edition issued		
0.02	May 01, 2011	1 to 2	1.1 Features revised		
		3	1.2 Ordering Information revised		
		4 to 13	1.3 Pin Configuration (Top View) revised		
		14	1.4 Pin Identification revised		
		15 to 17	1.5.1 30-pin products to 1.5.3 36-pin products revised		
		23 to 26	1.6 Outline of Functions revised		
0.03	Jul 28, 2011	1	1.1 Features revised		
1.00	Feb 21, 2012	1 to 40	1. OUTLINE revised		
		41 to 97	2. ELECTRICAL SPECIFICATIONS added		
2.00	Oct 25, 2013	1	Modification of 1.1 Features		
		3 to 8	Modification of 1.2 Ordering Information		
		9 to 22	Modification of package type in 1.3 Pin Configuration (Top View)		
		34 to 43	Modification of description of subsystem clock in 1.6 Outline of Functions		
		34 to 43	Modification of description of timer output in 1.6 Outline of Functions		
		34 to 43	Modification of error of data transfer controller in 1.6 Outline of Functions		
		34 to 43	Modification of error of event link controller in 1.6 Outline of Functions		
		45, 46	Modification of description of Tables in 2.1 Absolute Maximum Ratings		
		47	Modification of Tables, notes, cautions, and remarks in 2.2 Oscillator Characteristics		
		48	Modification of error of conditions of high level input voltage in 2.3.1 Pin characteristics		
		49	Modification of error of conditions of low level output voltage in 2.3.1 Pin characteristics		
		53 to 62	Modification of Notes and Remarks in 2.3.2 Supply current characteristics		
		65, 66	Addition of Minimum Instruction Execution Time during Main System Clock Operation		
		67 to 69	Addition of AC Timing Test Points		
		70 to 97	Addition of LS mode and LV mode characteristics in 2.5.1 Serial array unit		
		98 to 101	Addition of LS mode and LV mode characteristics in 2.5.2 Serial interface IICA		
		102 to 105	Addition of characteristics about conversion of internal reference voltage and temperature sensor in 2.6.1 A/D converter characteristics		
		107	Addition of characteristic in 2.6.4 Comparator		
		107	Deletion of detection delay in 2.6.5 POR circuit characteristics		
		109	Modification of 2.6.7 Power supply voltage rising slope characteristics		
		110	Modification of 2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics		
		110	Addition of characteristic in 2.8 Flash Memory Programming Characteristics		
		111	Addition of description in 2.10 Timing for Switching Flash Memory Programming Modes		